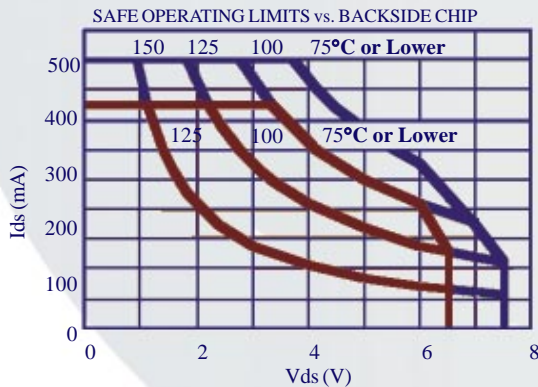
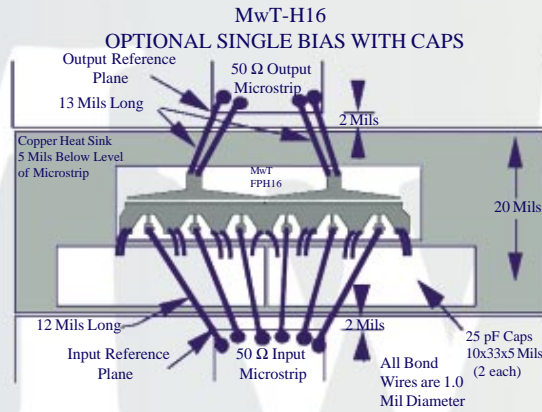
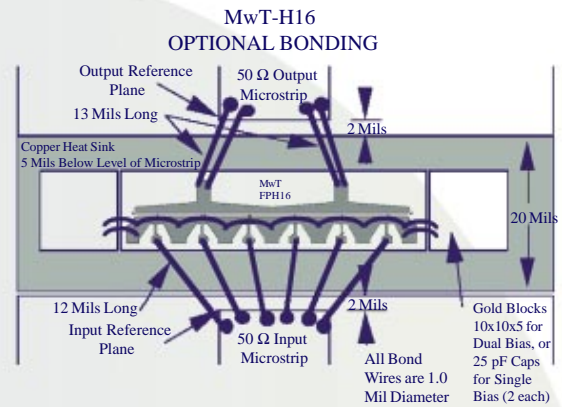
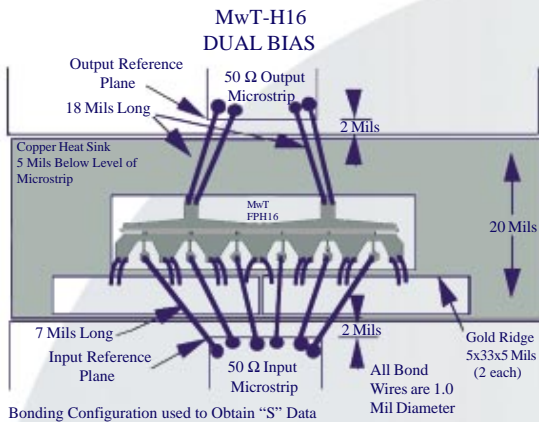


MwT-H16

32 GHz High Power

AlGaAs/InGaAs PHEMT



Absolute Maximum Continuous Maximum

MAXIMUM RATINGS AT Ta = 25°C

SYMBOL	PARAMETER	UNITS	CONT MAX ¹	ABSOLUTE MAX ²
VDS	Drain to Source Voltage	V	See Safe Operating Limits	
Tch	Channel Temperature	°C	+150	+175
Tst	Storage Temperature	°C	-65 to +150	+175
Pin	RF Input Power	mW	240	360

NOTES: 1. Exceeding any one of these limits in continuous operation may reduce the mean-time-to-failure below the design goals.
2. Exceeding any one of these limits may cause permanent damage.

BIN SELECTION

BIN#	1	2	3	4	5	6	7	8	9	10	11	12	13	14
IDSS (mA)	120-135	135-150	150-165	165-180	180-195	195-210	210-225	225-240	240-255	255-270	270-285	285-300	300-315	315-330

BIN ACCURACY STATEMENT

When placing order or inquiring, please specify BIN range, wafer no., if known, and screening level required.

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